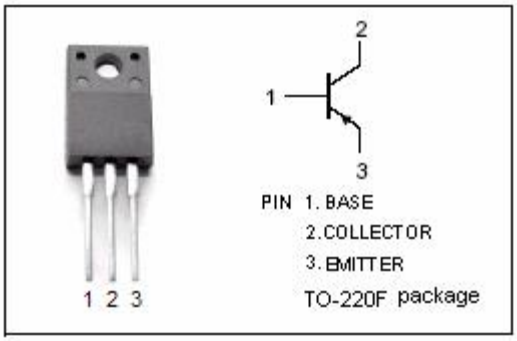
SPTECH Silicon PNP Power Transistor



DESCRIPTION

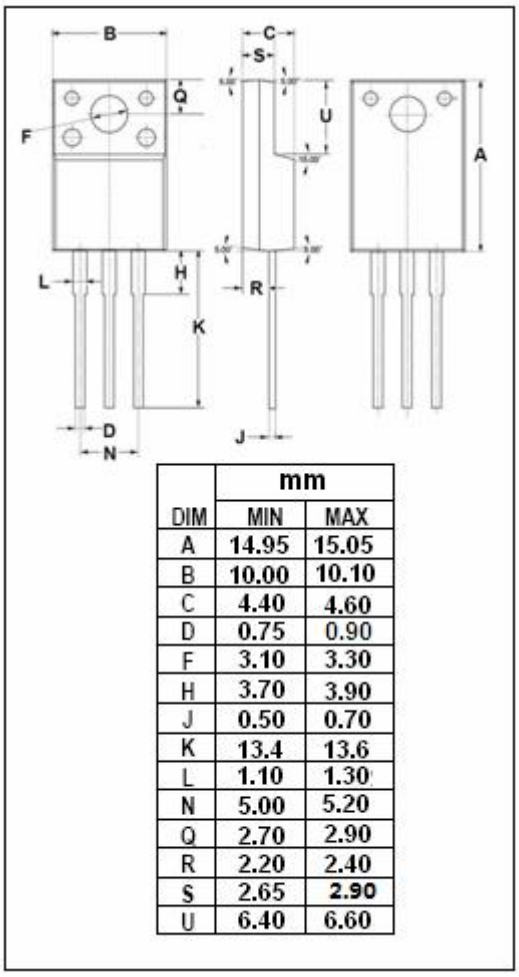
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -60V(Min)
- DC Current Gain-
  : h_{FE}= 60(Min)@ (V_{CE}= -2V, I_C= -2A)
- Low Saturation Voltage-
  : $V_{CE(sat)}$= −0.3V(Max)@ (I_C= -6A, I_B= -0.3A)

APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-12	A
P_C	Collector Power Dissipation @T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

SPTECH Silicon PNP Power Transistor

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA ; I_B= 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -50 μ A ; I_C= 0	-5			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -8A; I_B= -0.4A			-0.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= -8A; I_B= -0.4A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V ; I_E=0			-10	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0			-10	μ A
h_{FE-1}	DC Current Gain	I_C= -1A ; V_{CE}= -2V	100			
h_{FE-2}	DC Current Gain	I_C= -2A ; V_{CE}= -2V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C= -1A ; V_{CE}= -10V		90		MHz

◆ **h_{FE-2} Classifications**

D	E	F
60-120	100-200	160-320